

## Hund's rule, spin blockade, and the Aufbau principle in strongly confined semiconductor quantum dots

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2000 Europhys. Lett. 50 243

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(received 24 November 1999; accepted in final form 2 February 2000)

PACS. 73.20.Dx – Electron states in low-dimensional structures (superlattices, quantum well structures and multilayers).

**Abstract.** – The ground-state configuration of a system of  $N$  electrons or holes ( $N = 1 \dots 8$ ) in strongly confined InAs, InP, and Si quantum dots (diameter  $\sim 30$  Å) is calculated using pseudopotential single-particle energies and wave functions as input to the many-body expansion of the total energy. The validity of generally accepted “rules of level occupation” (Hund’s rule, Aufbau principle, and single spin-flip rule) is examined. We find that while Hund’s rule is generally obeyed, deviations from the Aufbau principle are common when single-particle energy levels are separated by a few meV. We also find a few instances where the single spin-flip rule is violated, leading to “spin blockade” in linear conductance.

When a quantum dot is weakly coupled to an electron reservoir, either via a gate structure [1–4] or an STM tip [5, 6], one can load, one by one,  $N$  electrons or holes into the dot by changing the gate voltage or the tip-substrate bias. The ability to successively load carriers into the dot enables one to study the “rules of level occupation” determining the sequence in which the energy levels of the dot are occupied. These rules are best illustrated by considering a dot with a pair of spatially degenerate single-particle energy levels  $e_{a1}$ ,  $e_{a2}$  and a non-degenerate energy level  $e_b$  such that the single-particle energies obey  $(e_{a1}) = (e_{a2}) < (e_b)$ .

i) *Hund’s rule*: Degenerate single-particle levels are occupied with a maximum number of unpaired electrons. For example, the transition from  $N = 1$  to  $N = 2$  electrons will prefer

$$e_{a1} \xrightarrow{\text{Hund}} e_{a1} e_{a2} \quad (1a)$$

over

$$= e$$

$$e_{a1} \xrightarrow{\text{Non--}} e_{a2}$$

ii) *The Aufbau principle*: Non-degenerate single-particle levels are occupied in order of increasing single-particle energy. For example, the  $N = 2$  to  $N = 3$  transition would prefer to



effective Hamiltonian involving only the conduction band electrons, provided that the electron-

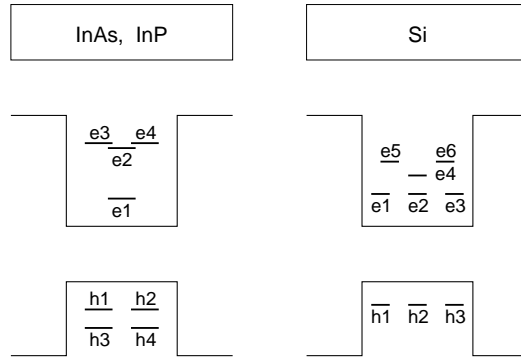


Fig. 1 – Schematic diagram of the near band-edge single-particle energy levels of InAs, InP, and Si spherical quantum dots. The valence band levels are denoted as  $h_1, h_2$ , etc. in order of decreasing energy starting from the valence band maximum, while the conduction band levels are denoted as  $e_1, e_2$ , etc. in order of increasing energy starting from the conduction band minimum.

degeneracy of the single-particle orbitals. Finally, the ground-state configuration for a given number  $N$  of electrons (or holes) is obtained by scanning different single configurations and diagonalizing the many-particle Hamiltonian (4) in search of the configuration with the lowest energy.

Our approximations are: i) The single-particle energies and wave functions are obtained by solving eq. (7) for a fixed, non-self-consistently screened potential. This approximation was examined in the case of an exciton [19] by comparing the electron-hole Coulomb integral obtained using non-self-consistent wave functions with the result of a self-consistent calculation. The difference was less than 5%. ii) The single-configuration approach used to diagonalize the many-particle Hamiltonian of eq. (4) neglects correlation effects due to configuration mixing. These effects were examined in ref. [18], and found to be small in strongly confined quantum dots. iii) Surface-polarization effects, which exist if the dielectric constant of the dot is different from that of the surrounding material, are neglected. This approximation is valid when  $\epsilon_{out} \sim \epsilon_{in}$ .

We consider here InAs, InP and Si spherical quantum dots having the  $T_d$  point-group symmetry. The surface dangling bonds are fully passivated. The single-particle energy levels calculated using pseudopotentials [15–17] have the general pattern shown in fig. 1. Each energy level in fig. 1 is doubly degenerate because of time reversal symmetry, and can be occupied by two particles (either electrons or holes). In the case of InAs and InP dots the two degenerate single-particle levels at the top of the valence band ( $h_1$  and  $h_2$ ) originate from the bulk  $\delta_8$  states, and have an  $s$ -like envelope function. The next two degenerate hole levels ( $h_3$  and  $h_4$ ) are also  $\delta_8$ -derived, but have  $p$ -like envelope functions. The electron level at the bottom of the conduction band ( $e_1$ ) originates from the bulk  $\delta_{6c}$  state and has an  $s$ -like envelope function. In InAs dots the next three electron levels ( $e_2, e_3$ , and  $e_4$ ) derive from the bulk  $\delta_{6c}$  state and have a  $p$ -like envelope function [15] ( $e_2$  is split from  $e_3$  and  $e_4$  because of spin=



holes are present in the quantum dot each of these two levels is occupied by one hole. In the diagonal approximation of eq. (6), the energy difference between the Hund configuration  $(h_1^1 h_2^1)$  and the non-Hund configuration  $(h_1^2 h_2^0)$  is  $E_2 = E_2(h_1^1 h_2^1) - E_2(h_1^2 h_2^0) = J_{h_1, h_2} - J_{h_1, h_1} - K_{h_1, h_2}$ . For a 30.3 Å diameter InAs dot we find  $E_2 = 166 - 172 - 6 = -12$  meV; for a 36.5 Å diameter InAs dot  $E_2 = 137 - 141 - 4 = -8$  meV. Thus, only about half of the stabilization of the Hund configuration comes from interelectronic exchange. The other half comes from the reduction in the Coulomb repulsion achieved by placing the two holes in different spatial orbitals. We find only one case where Hund's rule is violated: When six electrons are loaded into a 36.5 Å diameter quantum dot, two of them occupy the  $e_3$  level, while the  $e_4$  level (degenerate with  $e_3$ ) is empty. This is due to the fact that the coupling between the configurations  $(e_1^2 e_2^2 e_3^2)$  and  $(e_1^2 e_2^2 e_4^2)$ , which are degenerate at the single-particle level, is sufficiently strong to overcome the exchange and Coulomb energies gained by placing the electrons in the configuration  $(e_1^2 e_2^2 e_3^1 e_4^1)$ .

ii) *The Aufbau principle*: We find several instances where the Aufbau principle is not obeyed. For example, in InAs dots for  $N_{\text{holes}} = 3 \dots 7$  the hole levels  $h_3$  and  $h_4$  are occupied

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This work was supported by the U.S. DOE, OER-SC, Division of Materials Science, under Grant No. DE-AC36-98-GO10337.

#### REFERENCES

- [1] Mceuen P. L., Foxman E. B., Meirav U., Kastner M. A., Meir Y., Wingreen N.S. and Wind S. J., *Phys. Rev. Lett.*, **66** (1991) 1926.
- [2] Weis J., Haug R. J., von Klitzing K. and Ploog K., *Phys. Rev. Lett.*, **71** (1993) 4019.
- [3] Tarucha S., Austing D. G., Honda T., van der Hage R. J.